

SSCP1188GS3

PNP Switching Transistor

Features

VCB	VCE	VEB	IC
-40V	-32V	-5V	-2A

> Description

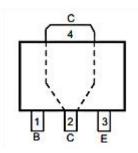
The PNP Transistor is designed for use in linear and switching applications. The device is housed in the SOT89-3 package, which is designed for telephony and professional communication equipment.

Applications

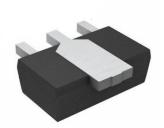
- General purpose switching and amplification
- Telephony and professional communication equipment

> Pin configuration

Top view



SOT89-3L



Bottom view

Ordering Information

Device	Package	Shipping
SSCP1188GS3	SOT89-3L	1000/Reel





\succ Absolute Maximum Ratings(T_A = 25°C unless otherwise noted)

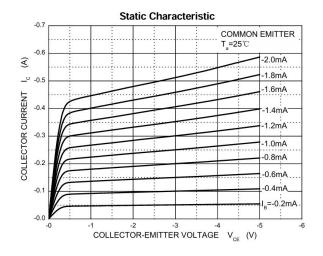
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector- Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	Ic	-2	Α
Collector Power Dissipation	Pc	500	mW
Junction Temperature	TJ	-55 to 150	$^{\circ}$
Storage Temperature	T _{STG}	-55 to 150	${\mathbb C}$

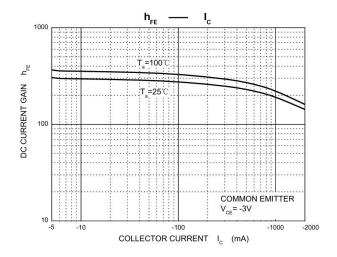
\triangleright Electrical Characteristics (T_A = 25°C unless otherwise noted)

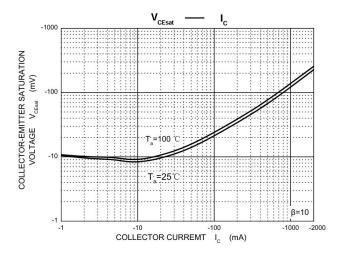
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	$I_{C} = -50uA, I_{E} = 0$	-40			V
Collector-emitter Breakdown Voltage	BV _{CEO}	$I_{C} = -1 \text{mA}, I_{B} = 0$	-32			V
Emitter -Base Breakdown Voltage	BV _{EBO}	$I_E = -50uA, I_C = 0$	-5			V
Collector Cutoff Current	I _{CBO}	V _{CB} = -20V, I _E = 0			-1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = -4V, I _C = 0			-1	μA
DC Current Gain	h _{FE}	V _{CE} = -3V, I _C = -0.5A	120		270	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -2A,I _B = -0.2A			-0.8	V
Transition frequency	f⊤	V _{CE} = -5V, I _C = -500mA f = 30MHz		100		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10V, I_E = 0,$ f = 1MHz		50		pF

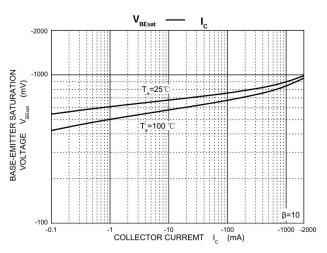


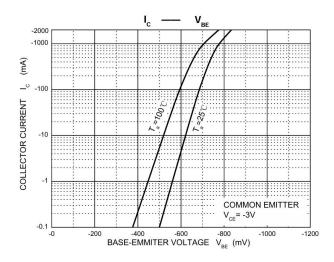
\succ Typical Performance Characteristics (T_A = 25°C unless otherwise noted)

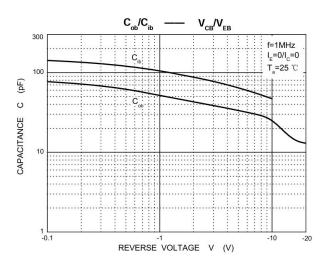




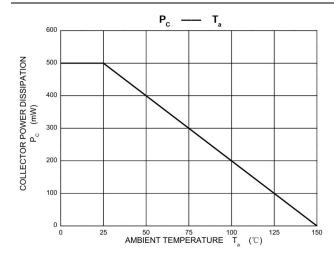






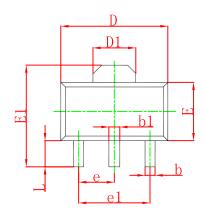


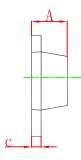




> Package Information

SOT89-3L

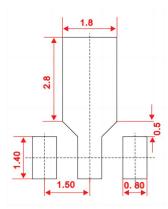




DIM	Millimeters			
ואווט	Min.	Тур.	Max.	
Α	1.400		1.600	
b	0.320		0.520	
b1	0.400		0.580	
С	0.350		0.440	
D	4.400		4.600	
D1		1.550		
Е	2.300		2.600	
E1	3.940		4.250	
е		1.500		
e1		3.000		
L	0.900		1.200	



Recommended Pad outline (Unit: mm)



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